

**METHODS FOR FORMING ELECTRONIC DEVICES INCLUDING
CAPACITOR STRUCTURES**

Abstract of the Disclosure

5 Methods for forming an electronic device can include forming a capacitor structure on a portion of a substrate with the capacitor structure including a first electrode on the substrate, a capacitor dielectric on the first electrode, a second electrode on the dielectric, and a hard mask on the second electrode. More particularly, the capacitor dielectric can be between the first 10 and second electrodes, the first electrode and the capacitor dielectric can be between the second electrode and the substrate, and the first and second electrodes and the capacitor dielectric can be between the hard mask and the substrate. An interlayer dielectric layer can be formed on the hard mask and on portions of the substrate surrounding the capacitor structure, and portions of the 15 interlayer dielectric layer can be removed to expose the hard mask while maintaining portions of the interlayer dielectric layer on portions of the substrate surrounding the capacitor structure. The hard mask can then be removed thereby exposing portions of the second electrode while maintaining the portions of the interlayer dielectric layer on portions of the substrate 20 surrounding the capacitor.